| Ref<br>#  | Hits  | Search Query   | DBs   | Default<br>Operator | Plurals | Time Stamp       |
|-----------|-------|--|---|---------------------|---------|------------------|
| S1        | 62675 | SiC silicon adj carbide and colloidial adj silica    | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR                  | ON      | 2005/10/13 12:03 |
| S2        | 1     | silicon adj carbide and colloidial<br>adj silica     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/02/07 17:53 |
| <b>S3</b> | 0     | cmp and colloidial adj silica                        | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/02/07 17:53 |
| S4        | 1     | Polishing and colloidial adj silica                  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/02/07 17:54 |
| S5        | 22    | colloidial adj silica                                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON .    | 2005/02/07 18:01 |
| S6        | 2304  | polishing şame silicon adj carbide<br>ं              | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/02/07 18:01 |
| S7        | 963   | polishing same silicon adj carbide and semiconductor | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/02/07 18:23 |

| S8  | 94         | ("5964942" "5989755" "6140210" "6328796" "6497763" "5635269" "5676723" "6127068" "6248395" "6534228" "6150023" "5584898" "5670253" "5913974" "6284628" "6322427" "6362076" "6596610" "6720640" "5686364" "6261928" "6120353" "5582897" "5591502" "5705421" "5705423" "5744401" "5855998" "5981392" "6004866" "6117750" "6193585" "5352277" "5438951" "5500607" "5543648" "5571373" "5733177" "5736226" | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR . | ON . | 2005/02/07 18:23 |
|-----|------------|--|---|------|------|------------------|
|     |            | "5767691" "5776246" "5869387"<br>"5874130" "6008128" "6051063"<br>"6121117" "6171982" "6189546"<br>"6230720" "6238272").pn.  |   |      |      |                  |
| S9  | <b>272</b> | polishing same silicon adj carbide same semiconductor  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON   | 2005/02/08 10:46 |
| S10 | 204        | angled ion implantation  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ  | ON   | 2005/02/07 19:08 |
| S11 | 6          | gate shadowing   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ  | ON   | 2005/02/07 19:08 |
| S12 | 47         | polishing same silicon adj carbide<br>adj substrate  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON   | 2005/02/08 12:59 |
| S13 | . 19       | polishing same silicon adj carbide<br>adj substrate and diamond  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON   | 2005/02/08 11:30 |
| S14 | 6          | polishing same silicon adj carbide<br>adj substrate and silica   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON   | 2005/02/08 10:49 |
| S15 | 2          | ("5895583").PN.  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | OFF  | 2005/02/08 11:30 |

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| S16 | 1   | polishing same silicon adj carbide<br>adj substrate and oxidizing adj<br>atmosphere                            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 13:10 |
| S17 | 1   | 1996-007979.NRAN.  | DERWENT   | OR | OFF  | 2005/02/08 13:05 |
| S18 |     | polishing same silicon adj carbide<br>adj substrate and anneal   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 13:10 |
| S19 | 69  | silicon adj carbide adj substrate<br>and oxidizing adj atmosphere  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 14:25 |
| S20 | 11  | silicon adj carbide adj substrate<br>same oxidizing adj atmosphere   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON . | 2005/02/08 13:11 |
| S21 | 299 | silicon adj carbide adj substrate<br>and bonded  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 14:48 |
| S22 | 441 | silicon adj carbide adj substrate<br>and epitaxial adj growth  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 15:11 |
| S23 | 1   | silicon adj carbide adj substrate<br>and epitaxial adj growth and<br>polishing and oxidizing adj<br>atmosphere | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/08 15:38 |
| S24 | 30  | silicon adj carbide adj substrate<br>and epitaxial adj growth and<br>polishing and bonding                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/09 10:07 |
| S25 | 4   | silicon adj carbide adj substrate<br>same bonding and epitaxial adj<br>growth and polishing                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/09 10:29 |
| S26 | 108 | silicon adj carbide adj substrate<br>and epitaxial adj growth and<br>bonding                                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON   | 2005/02/09 10:16 |

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| S27 | 3     | silicon adj carbide adj substrate<br>and epitaxial adj growth and<br>bonding and RCA | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/02/09 10:18 |
| S28 | 15    | silicon adj carbide adj substrate<br>same bonding and epitaxial adj<br>growth        | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/02/09 10:35 |
| S29 | 66537 | SiC silicon adj carbide and RCA<br>SC1   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:33 |
| S30 | 3854  | silicon adj carbide and RCA SC1  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:36 |
| S31 | 1214  | silicon adj carbide and RCA SC1 and semiconductor                                    | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:37 |
| S32 | 1034  | silicon adj carbide adj substrate<br>and RCA SC1 and semiconductor                   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:37 |
| S33 | 1021  | silicon adj carbide adj substrate<br>same RCA SC1 and semiconductor                  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:38 |
| S34 | 0     | silicon adj carbide adj substrate<br>same RCA and polishing                          | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:39 |
| S35 | 0     | silicon adj carbide adj substrate<br>same sc1 and polishing                          | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:39 |
| S36 | 1     | silicon adj carbide adj substrate<br>same HF and polishing                           | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:40 |
| S37 | 0     | silicon adj carbide adj substrate<br>same cleaning same polishing                    | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:41 |
| S38 | 21    | silicon adj carbide adj substrate<br>same cleaning andpolishing                      | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR | ON | 2005/02/17 13:41 |

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| S39 | 1     | silicon adj carbide adj substrate<br>same cleaning and polishing  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/02/17 13:42 |
| S40 | 6     | silicon adj carbide adj substrate<br>same clean and polishing   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/02/17 13:43 |
| S41 | 6     | silicon adj carbide adj substrate<br>and (RCA or Hydroflouric) and<br>polishing   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/02/17 19:29 |
| S42 | 3     | silicon adj carbide adj substrate<br>and (RCA and Hydrofluoric) and<br>polishing  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/02/17 19:29 |
| S43 | 28140 | colloidal adj silica  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | OFF | 2005/08/04 19:44 |
| S44 | 1654  | colloidal adj silica and silicon adj<br>carbide   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | OFF | 2005/08/04 19:45 |
| S45 | 2318  | colloidal adj silica and silicon adj<br>carbide   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/04 19:46 |
| S46 | 645   | colloidal adj silica and silicon adj<br>carbide and polishing   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/04 19:46 |
| S47 | 143   | colloidal adj silica and silicon adj<br>carbide and polishing and "438"/\$.<br>ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/04 19:51 |
| S48 | 15    | colloidal adj silica and silicon adj<br>carbide near5 (substrate or wafer)<br>and polishing and "438"/\$.ccls.                        | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR · | ON  | 2005/08/04 19:52 |
| S49 | 18    | colloidal adj silica and silicon adj<br>carbide near5 (substrate or wafer)<br>and polishing and ("438"/\$.ccls. or<br>"257"/\$.ccls.) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/05 14:24 |

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| S50 | 4     | colloidal adj silica and silicon adj<br>carbide adj (substrate or wafer)<br>and polishing and ("438"/\$.ccls. or<br>"257"/\$.ccls.) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/05 14:39 |
| S51 | 290   | colloidal adj silica and surface adj<br>roughness and ("438"/\$.ccls. or<br>"257"/\$.ccls.)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/08/05 14:40 |
| S52 | 5     | (("5877070") or ("6833562")).PN.  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | OFF | 2005/08/05 15:57 |
| S53 | 65019 | SiC silicon adj carbide and colloidial adj silica and rms   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/10/13 12:03 |
| S54 | 0     | (SiC or silicon adj carbide) and colloidial adj silica and rms  | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | ON  | 2005/10/13 12:04 |
| S55 | 0     | (SiC or silicon adj carbide) and colloidial adj silica and rms  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/10/13 12:05 |
| S56 | 0     | (SiC or silicon adj carbide) and colloidial adj silica and nm   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/10/13 12:05 |
| S57 | 2     | (SiC or silicon adj carbide) and colloidial adj silica  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR   | ON  | 2005/10/13 12:05 |
| S58 | 310   | 438/478.ccls.   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR . | OFF | 2005/10/13 13:06 |
| S59 | 436   | 438/689.ccls.   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB              | OR   | OFF | 2005/10/13 13:21 |
| S60 | 170   | 438/478.ccls.   | US-PGPUB;<br>JPO  | OR   | OFF | 2005/10/13 13:07 |
| S61 | 1192  | 438/689.ccls.   | US-PGPUB  | OR   | OFF | 2005/10/13 14:30 |
| S62 | 181   | 438/689.ccls. and slurry  | US-PGPUB  | OR   | OFF | 2005/10/13 14:39 |
| S63 | 100   | 438/689.ccls. and slurry and silica   | US-PGPUB  | OR   | OFF | 2005/10/13 14:39 |

| S64 | 43              | 438/689.ccls. and slurry and colloidal adj silica               | US-PGPUB                                   | OR | ON | 2005/10/13 14:43 |
|-----|-----------------|---|--|----|----|------------------|
| S65 | 20              | 438/689.ccls. and slurry and colloidal adj silica and roughness | US-PGPUB                                   | OR | ON | 2005/10/13 14:54 |
| S66 | 3               | 438/689.ccls. and slurry and colloidal adj silica and anneal    | US-PGPUB                                   | OR | ON | 2005/10/13 14:54 |
| S67 | . 1             | 438/692.ccls. and slurry and colloidal adj silica and anneal    | US-PGPUB                                   | OR | ON | 2005/10/13 14:55 |
| S68 | 1               | 438/767.ccls. and slurry and colloidal adj silica and anneal    | US-PGPUB                                   | OR | ON | 2005/10/13 14:55 |
| S69 | 19 <sup>.</sup> | 438/767.ccls.   | US-PGPUB                                   | OR | ON | 2005/10/13 14:56 |
| S70 | 264             | 438/767.ccls.   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/10/13 14:56 |
| S71 | 293             | 438/931.ccls.   | USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/10/13 14:58 |